

Amendments to the Specification:

Please replace paragraph [0042] on page 17 with the following amended version of that paragraph:

As shown in Figure 24, with the choice of suitable chemistry and processing conditions, the film can be deposited in an entirely bottom-up manner, with the highest growth rate in the smallest structures.

Please replace paragraph [0049] on page 26 with the following amended version of that paragraph:

Methods for selectively depositing a solid material on a substrate having gaps of dimension on the order of about 100 nm or less are disclosed. The methods involve exposing the substrate to a precursor of a solid material, such that the precursor forms liquid regions in at least some of the gaps, followed by exposing the substrate to conditions that evaporate the liquid precursor from regions outside the gaps but maintain at least some of the liquid regions in the gaps. The liquid precursor remaining in the gaps is then converted to solid material, thereby selectively ~~filling~~ filling the gaps with the material.